

TO-92 Plastic-Encapsulate Transistors

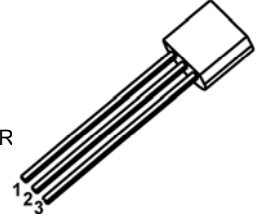
2SC1213 TRANSISTOR (NPN)

FEATURES

- Low Frequency Amplifier
- Complementary Pair With 2SA673

TO - 92

1. EMITTER
2. COLLECTOR
3. BASE



MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	35	V
V_{CEO}	Collector-Emitter Voltage	35	V
V_{EBO}	Emitter-Base Voltage	4	V
I_C	Collector Current	0.5	A
P_C	Collector Power Dissipation	400	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	312	$^{\circ}\text{C}/\text{W}$
T_j	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55~+150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=0.01\text{mA}, I_E=0$	35			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}, I_B=0$	35			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=0.01\text{mA}, I_C=0$	4			V
Collector cut-off current	I_{CBO}	$V_{CB}=20\text{V}, I_E=0$			0.5	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=3\text{V}, I_C=0$			0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=3\text{V}, I_C=10\text{mA}$	60		320	
	$h_{FE(2)}$	$V_{CE}=3\text{V}, I_C=500\text{mA}$	10			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=150\text{mA}, I_B=15\text{mA}$			0.6	V
Base-emitter voltage	V_{BE}	$V_{CE}=3\text{V}, I_C=10\text{mA}$			0.75	V

CLASSIFICATION OF $h_{FE(1)}$

RANK	B	C	D
RANGE	60-120	100-200	160-320